

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

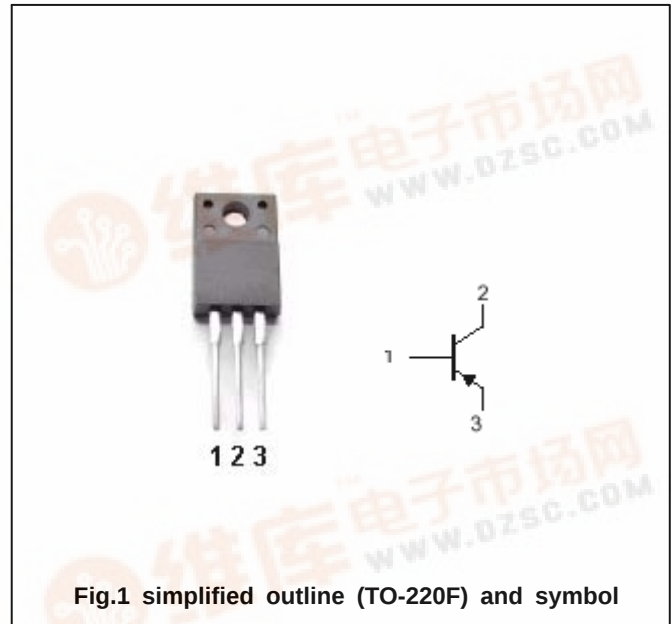
2SB1566

DESCRIPTION

- With TO-220F package
- Excellent DC current gain characteristics
- Low collector saturation voltage
- Wide SOA (safe operating area)
- Complement to type 2SD2395

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-4.5	A
P_C	Collector dissipation	$T_a=25$	2	W
		$T_C=25$	25	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1mA ; I_B=0$	-50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-50 \mu A ; I_E=0$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-50 \mu A ; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2A ; I_B=-0.2A$			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2A ; I_B=-0.2A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V ; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-7V ; I_C=0$			-1.0	μA
h_{FE}	DC current gain	$I_C=-0.5A ; V_{CE}=-5V$	100		320	
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=-10V ; f=1MHz$		40		pF
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-5V$		60		MHz

◆ h_{FE} Classifications

E	F
100-200	160-320

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PACKAGE OUTLINE

